



Bipolar NPN Bare Die – BTN6134

Part Description

The BTN6134 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. PNP Complement is BTP6134.

Key Parameters:

- VCBO = 40V
- VCEO = 32V
- VEBO = 5V
- hFE = 82-360 @ VCE = 3V, IC = 0.5A
- VCE(Sat) = 0.8V @ IC = 2A, IB = 200mA
- fT = 100 MHz @ VCE = 5V, IE = 0A
- COBO = 30pF @ VCB = 10V

Features

Low VCE(sat). Designed to provide performance equivalent to ROHM 2SD1380

Die Size (Unawn)

1020 μ m X 1020 μ m, 40 Mils X 40 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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